

2SD2195 / 2SD1980 / 2SD1867

- 1) Darlington connection for high DC current gain.
- 2) Built-in resistor between base and emitter.
- 3) Built-in damper diode.
- 4) Complements the 2SB1580 / 2SB1316.

Parameter		Symbol	Limits	Unit
Collector-base voltage		V _{CB0}	100	V
Collector-emitter voltage		V _{CE0}	100	V
Emitter-base voltage		V _{EB0}	6	V
Collector current		I _C	2	A(DC)
			3	A(Pulse) *1
Collector power dissipation	2SD2195	P _C	2	W *2
	2SD1980		1	W(T _C =25°C)
	2SD1867		10	
				1
Junction temperature		T _J	150	°C
Storage temperature		T _{st0}	-55~+150	°C

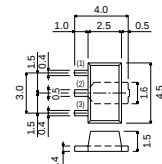
Storage temperature	Tstg	-55~+150
*1 Single pulse Pw=100ms *2 When mounted on a 40 x 40 x 0.7 mm ceramic board. *3 Printed circuit board, 1.7mm thick, collector plating 100mm² or larger.		

Type	2SD2195	2SD1980	2SD1867
Package	MPT3	CPT3	ATV
hFE	1k-10k	1k-10k	1k-10k
Marking	DP®	—	—
Code	T100	TL	TV2
Basic ordering unit (pieces)	1000	2500	2500

* Denotes h_{EE}

$R_1 = 3.5\text{k}\Omega$ B : Base
 $R_2 = 300\Omega$ C : Collector
 E : Emitter

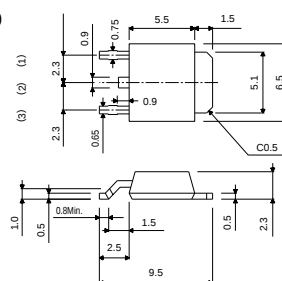
2SD2195



ROHM : MPT3
EIAJ : SC-62

- (1) Base(Gate)
- (2) Collector(Drain)
- (3) Emitter(Source)

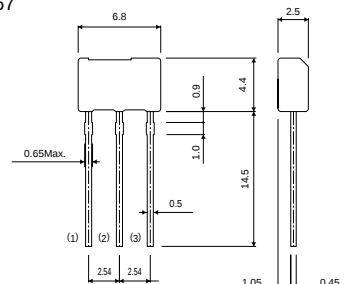
2SD1980



ROHM : CPT3
EIAJ : SC-63

- (1) Base(Gate)
- (2) Collector(Drain)
- (3) Emitter(Source)

2SD1867



Taping specifications

ROHM : ATV

- (1) Emitter
- (2) Collector
- (3) Base

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	100	—	—	V	$I_C = 50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	100	—	—	V	$I_C = 5mA$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 100V$
Emitter cutoff current	I_{EBO}	—	—	3	mA	$V_{EB} = 5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	1.5	V	$I_C = 1A, I_B = 1mA$
DC current transfer ratio	h_{FE}	1000	—	10000	—	$V_{CE} = 2V, I_C = 1A$
Output capacitance	C_{ob}	—	25	—	pF	$V_{CE} = 10V, I_C = 0A, f = 1MHz$

* Measured using pulse current.